



SAND2019-14557PE

MICROSTRUCTURE MORPHOLOGY OF Bicontinuous Nanocomposites Thin-films DURING PHYSICAL VAPOR DEPOSITION (PVD)

REMI DINGREVILLE, CINT, SANDIA NATIONAL LABORATORIES

MULTI-DISCIPLINARY & COLLABORATIVE RESEARCH

- **Graduate students**

M. Powers (Ph.D., U. Michigan), E. Hermann (UNC)

- **Postdocs**

J. Stewart (SNL), D. Montes de Oca Zapiain (SNL)

- **External Collaborators**

A. Misra (U. Michigan), K. Baldwin (LANL), N. Li (LANL)

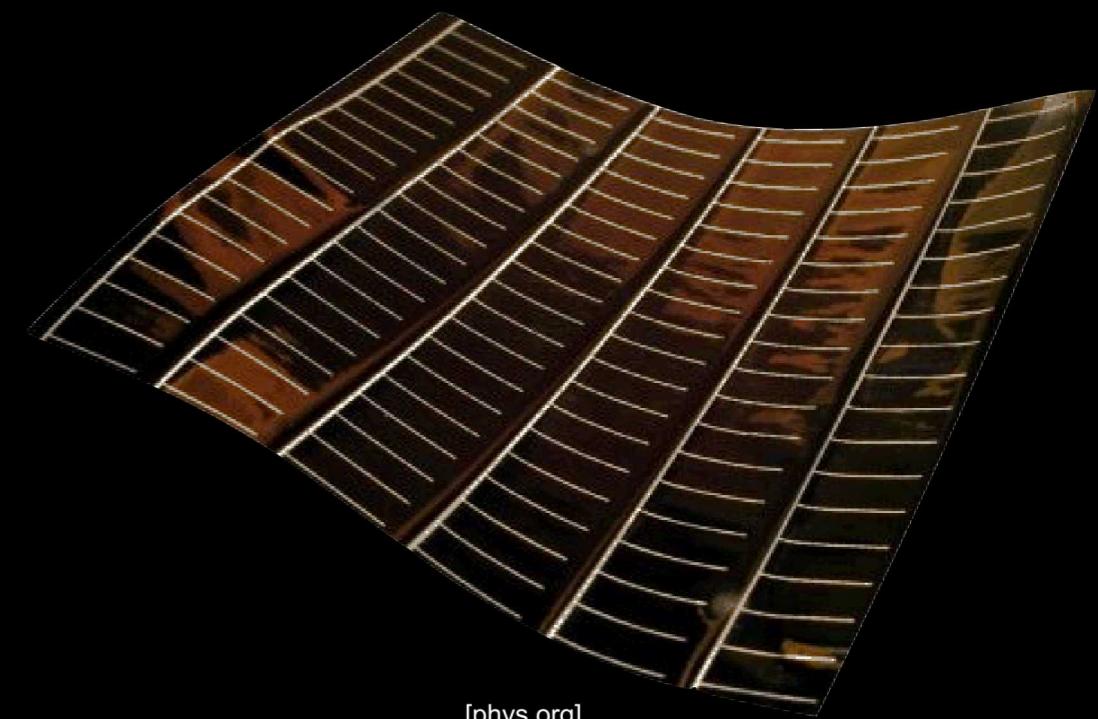
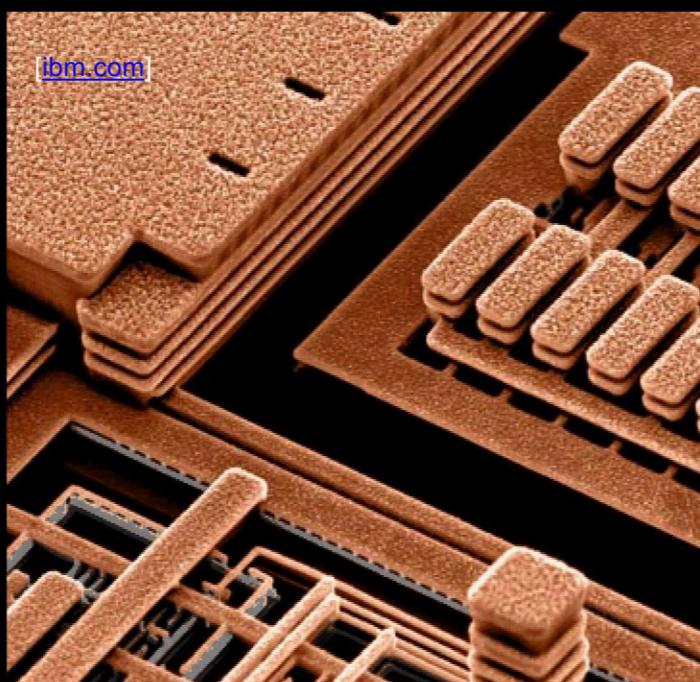
- **Funding**



WE USE THIN-FILM COATINGS TO ACHIEVE TARGETED TECHNOLOGICAL FUNCTIONALITIES

Decorative

Optical



Mechanical

Microelectronic

Photovoltaic

THE HISTORY OF PVD IS CLOSELY LINKED TO THE DISCOVERY OF ELECTRICITY AND MAGNETISM

VIII. *Experimental Researches in Electricity.—Thirteenth Series.* By MICHAEL FARADAY, Esq., D.C.L. F.R.S. Fullerian Prof. Chem. Royal Institution, Corr. Memb. Royal and Imp. Acadd. of Sciences, Paris, Petersburgh, Florence, Copenhagen, Berlin, &c. &c.

Received February 22,—Read March 15, 1838.

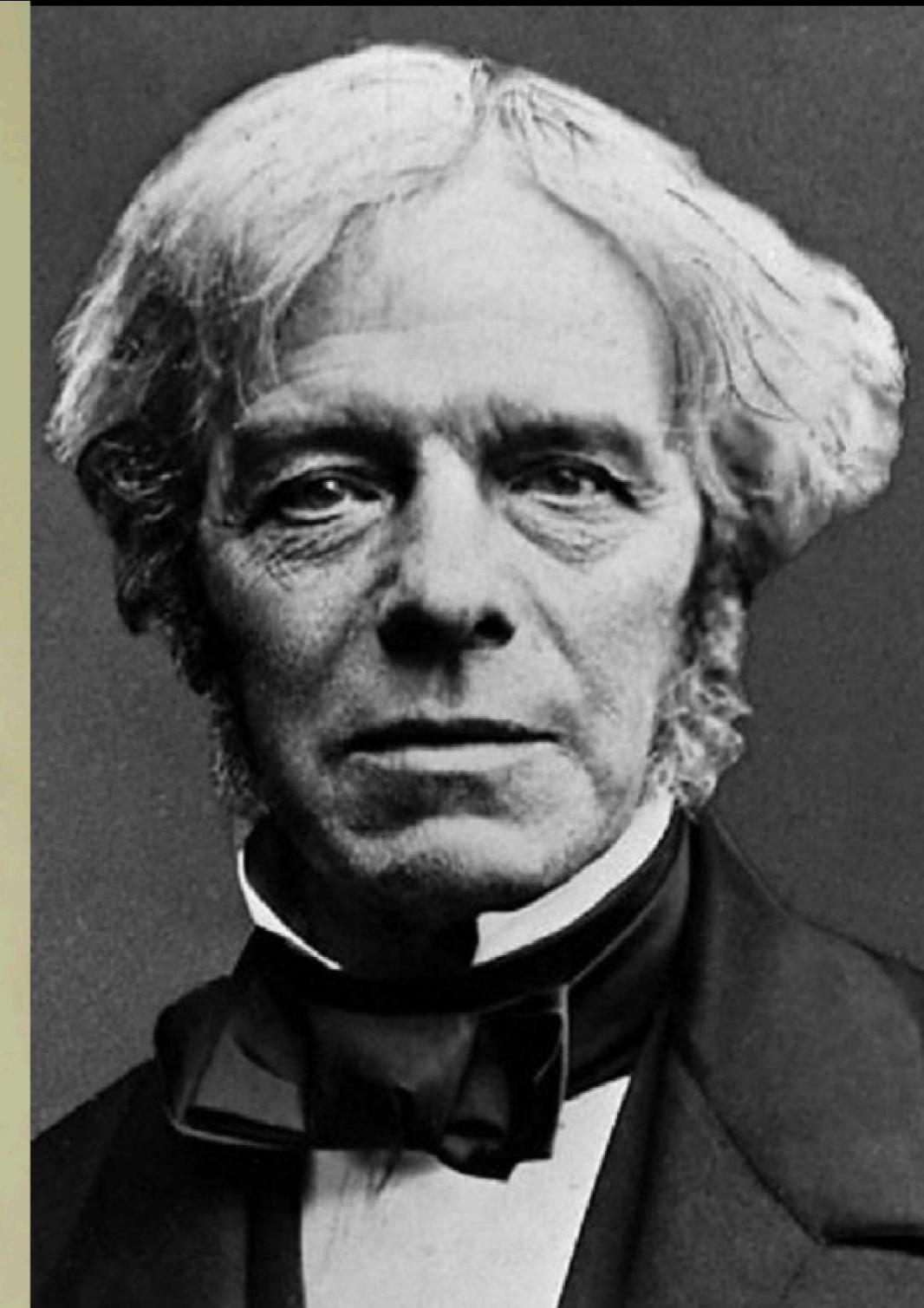
§. 18. *On Induction (continued).* ¶ ix. *Disruptive discharge (continued)—Peculiarities of positive and negative discharge either as spark or brush—Glow discharge—Dark discharge.—¶ x. Convection, or carrying discharge. ¶ xi. Relation of a vacuum to electrical phenomena.* §. 19. *Nature of the electrical current.*

¶ ix. *Disruptive discharge (continued).*

1480. LET us now direct our attention to the general difference of the positive and negative disruptive discharge, with the object of tracing, as far as possible, the cause of that difference, and whether it depends on the charged conductors principally, or on the interposed dielectric; and as it appears to be great in air and nitrogen (1476.), let us observe the phenomena in air first.

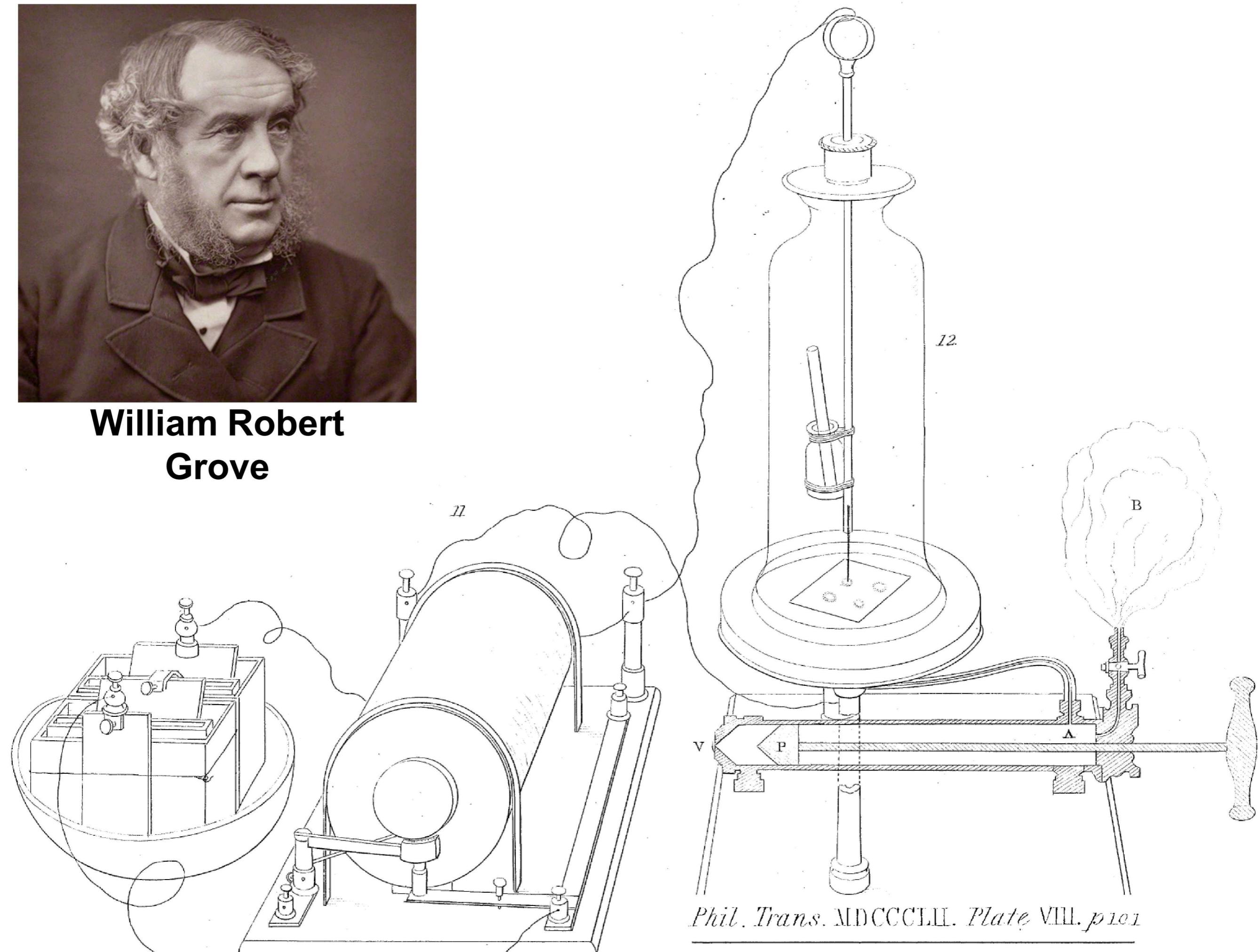
1481. The general case is best understood by a reference to surfaces of considerable size rather than to points, which involve (as a secondary effect) the formation of currents (1562.). My investigation, therefore, was carried on with balls and terminations of different diameters, and the following are some of the principal results.

1482. If two balls of very different dimensions, as for instance one, half an inch, and the other three inches, in diameter, be arranged at the ends of rods so that either can be electrified by a machine and made to discharge by sparks to the other, which is at the same time uninsulated; then, as is well known, far longer sparks are obtained





**William Robert
Grove**



T. A. EDISON.

ART OF PLATING ONE MATERIAL WITH ANOTHER.

No. 526,147.

Patented Sept. 18, 1894.

Fig. 1.

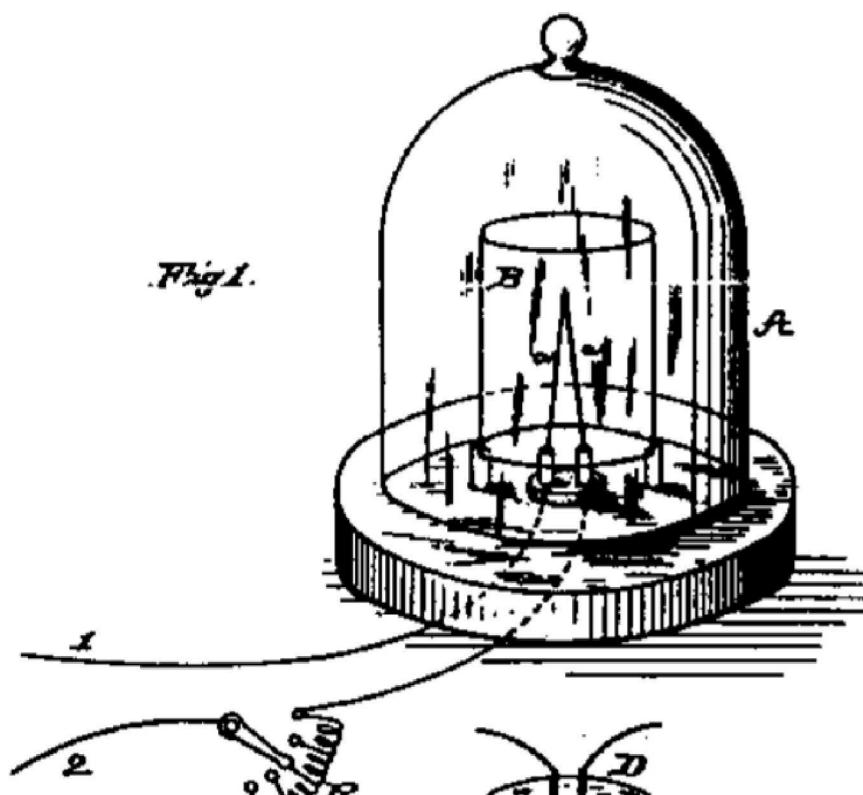
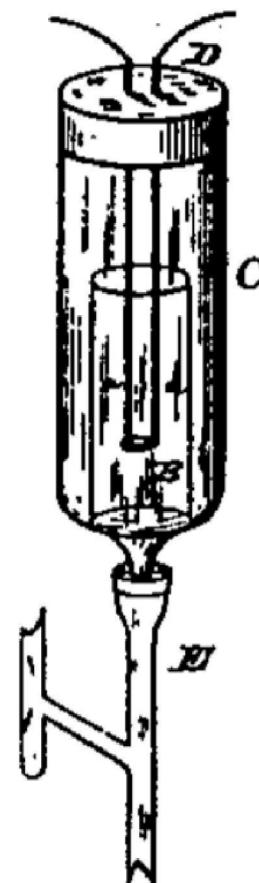


Fig. 2.



WITNESSES:

Ed. Reinhard
W. W. Dyer

INVENTOR:

Thomas A. Edison
By Rich & A. Dyer

THE EDISON NEW STANDARD PHONOGRAPH.

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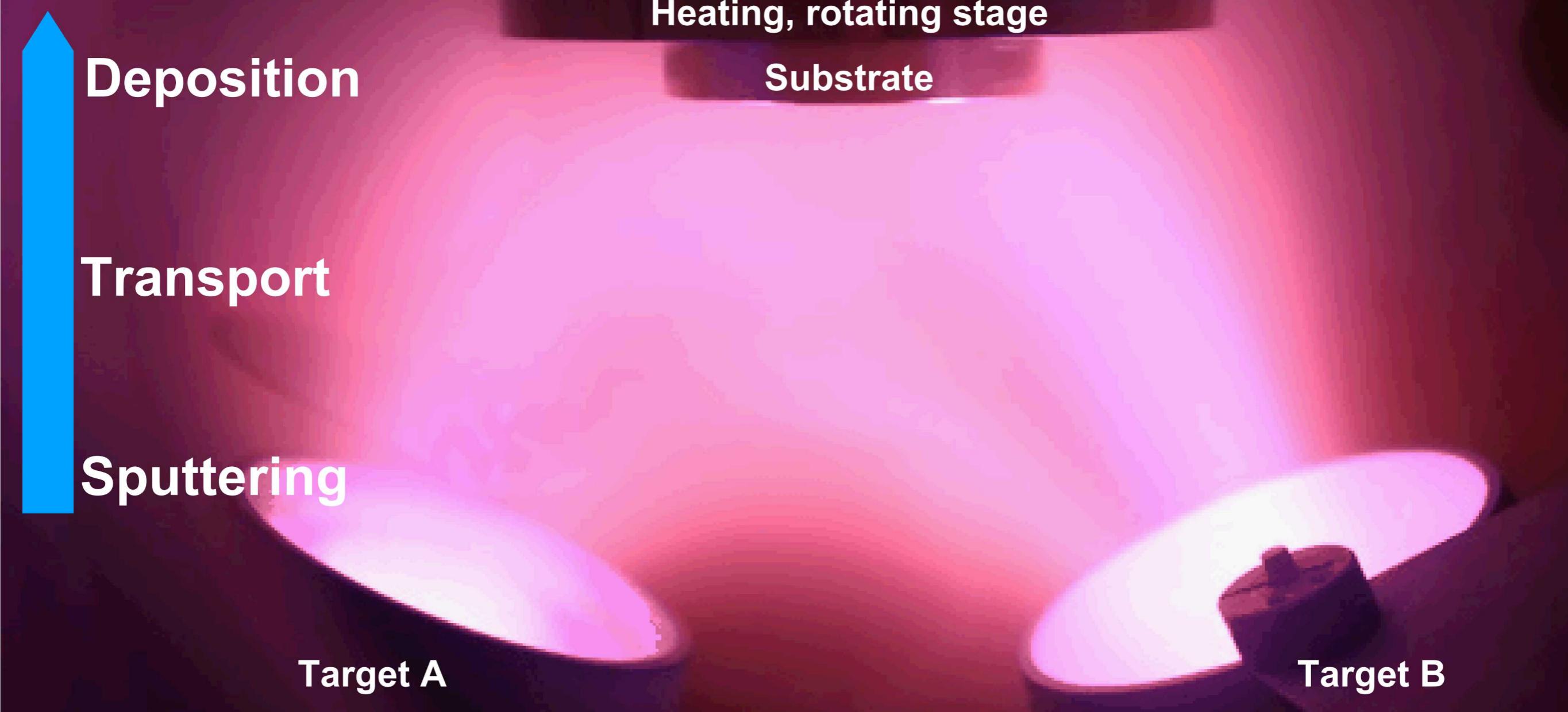
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PVD IS A SYNTHESIS ROUTE TO DEPOSIT AND ENGINEER THIN-FILMS ONE ATOM AT A TIME

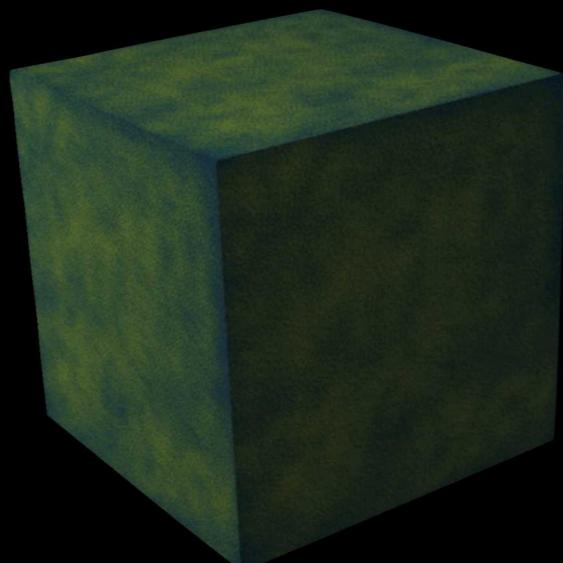


DIFFRENT PVD SYNTHESIS ROUTES ENABLE (SOME) CONTROL OF THE MORPHOLOGY

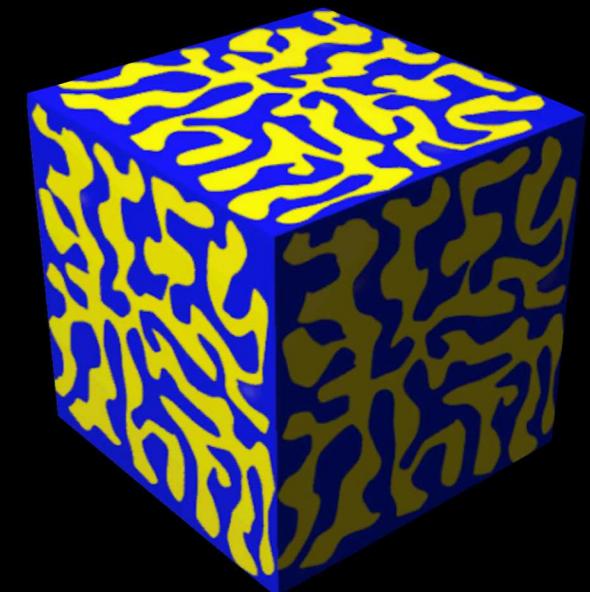
RT deposition

+

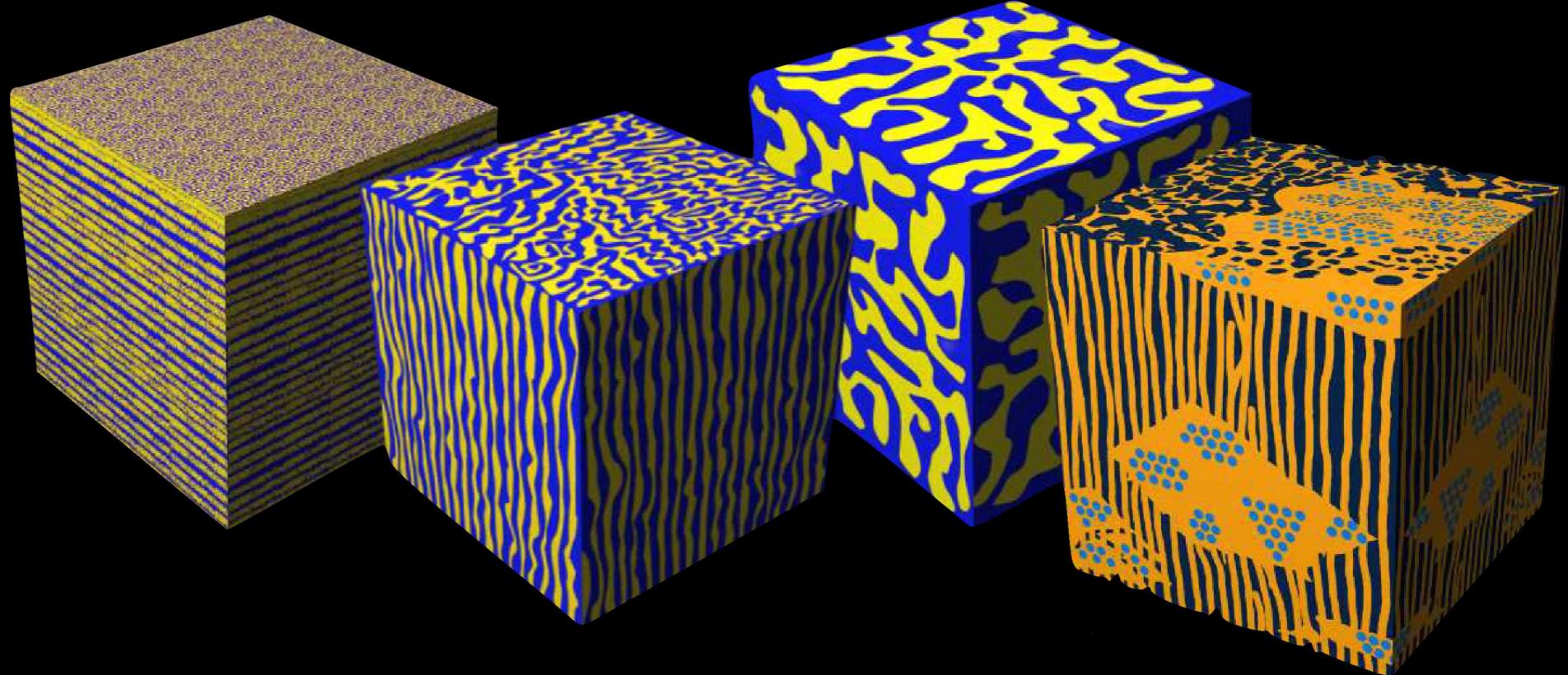
Annealing



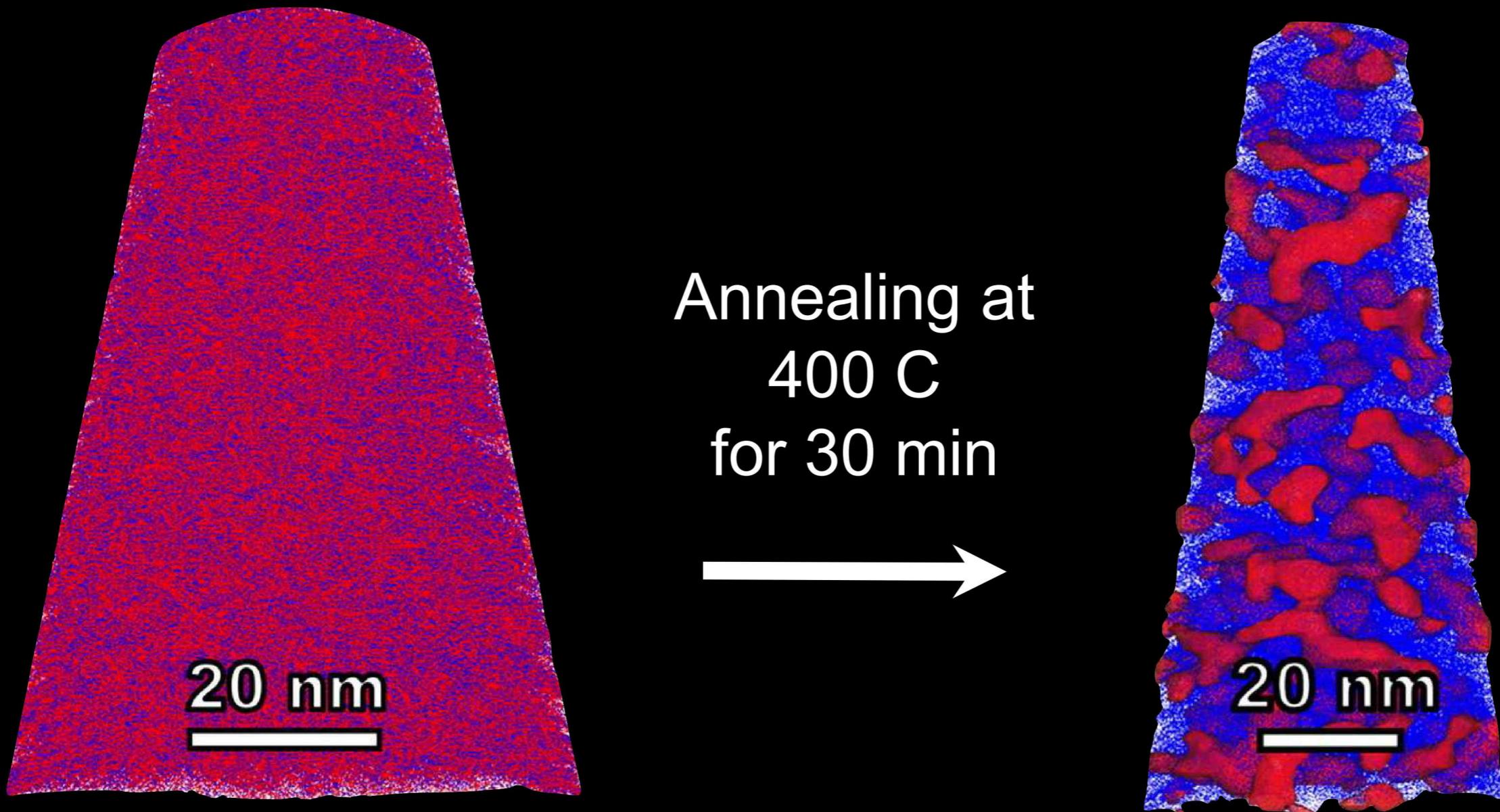
Annealing



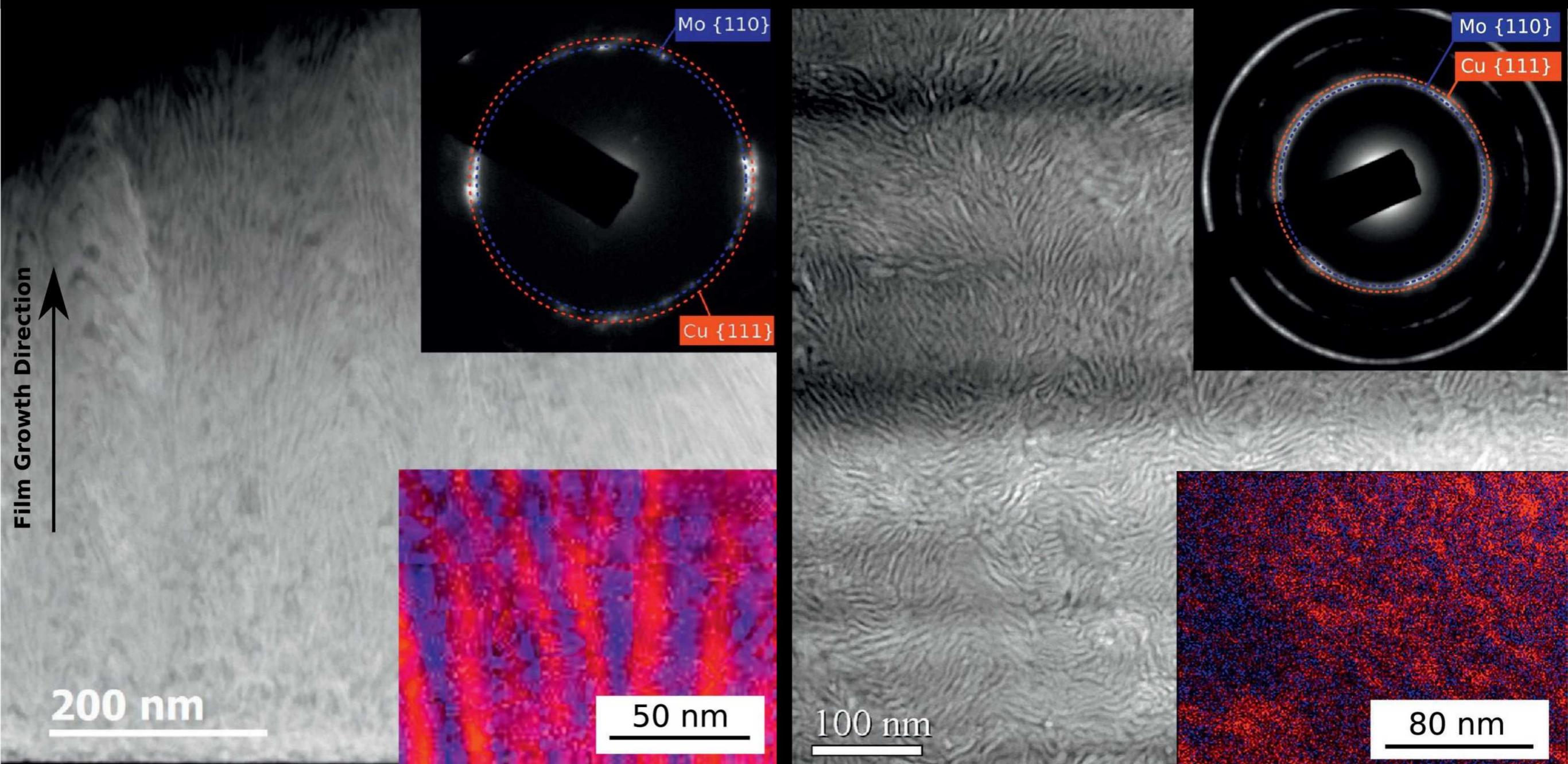
Heating
during
deposition



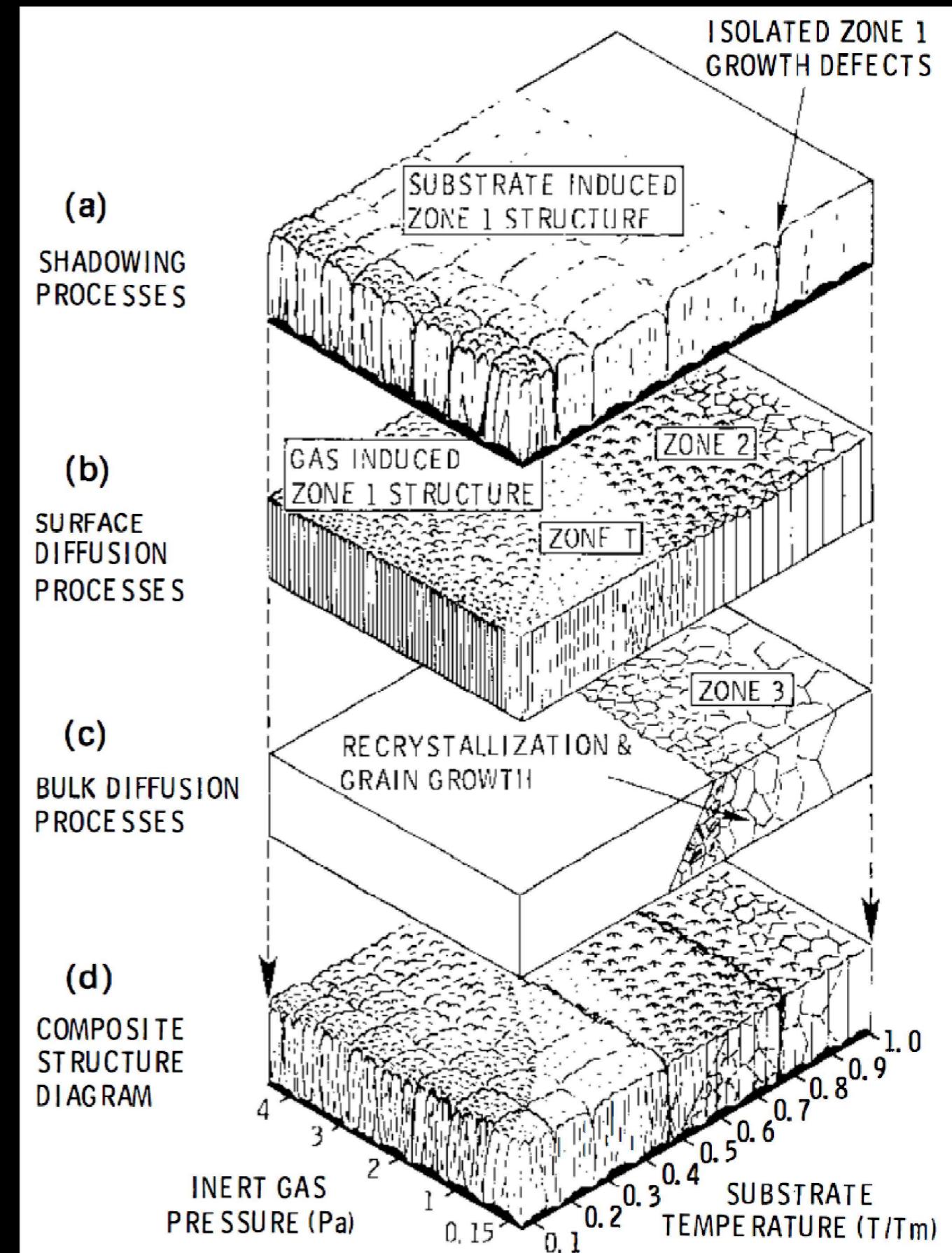
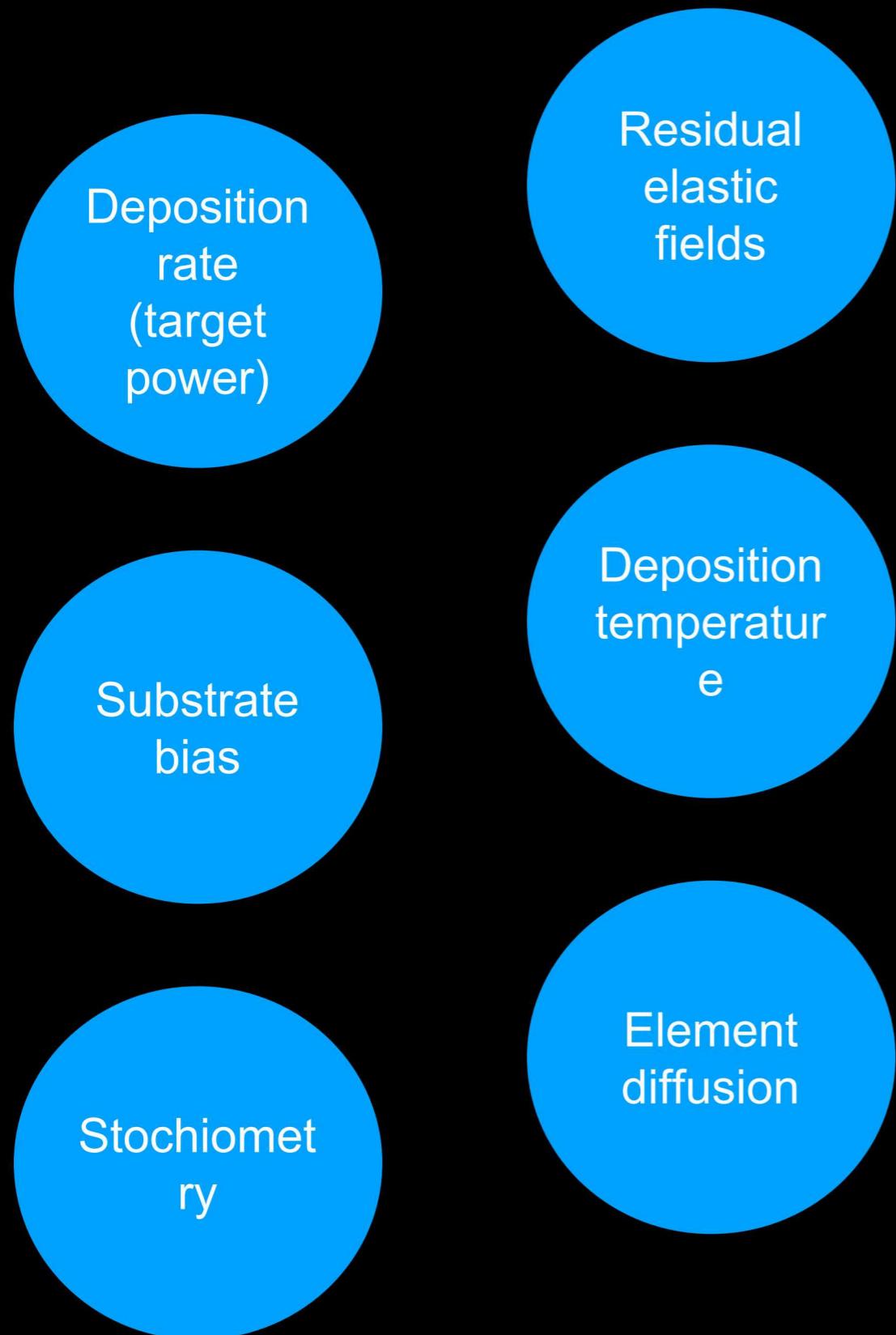
EXAMPLE 1: PHASE SEPARATION IN Cu-Ta DUE TO CO-DEPOSITION FOLLOWED BY ANNEALING



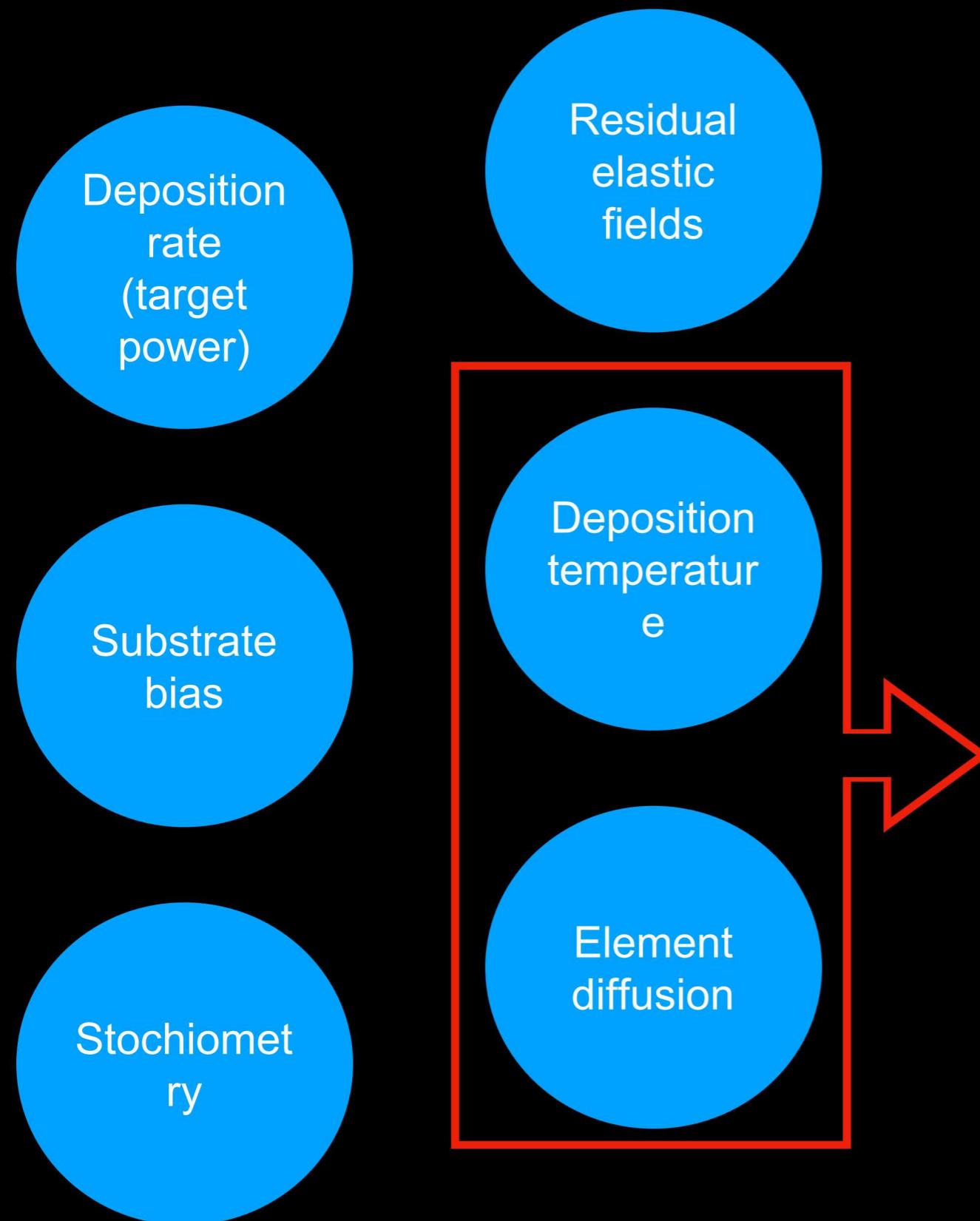
EXAMPLE 2: PHASE SEPARATION IN Cu-Mo BY CHANGING THE DEPOSITION TEMPERATURE AND FLUX



THERE ARE MULTIPLE VARIABLES AFFECTING THE RESULTING MICROSTRUCTURE



THE CHARACTERISTIC SIZE IS GOVERNED BY THE COMPETITION BETWEEN BULK AND SURFACE ORDERING



BULK:

$$\ell_{\text{bulk}} = \sqrt{2D\tau}$$

THIN-FILM:

$$\ell_{\text{thin film}} = \sqrt{\frac{2D\lambda}{\nu}}$$

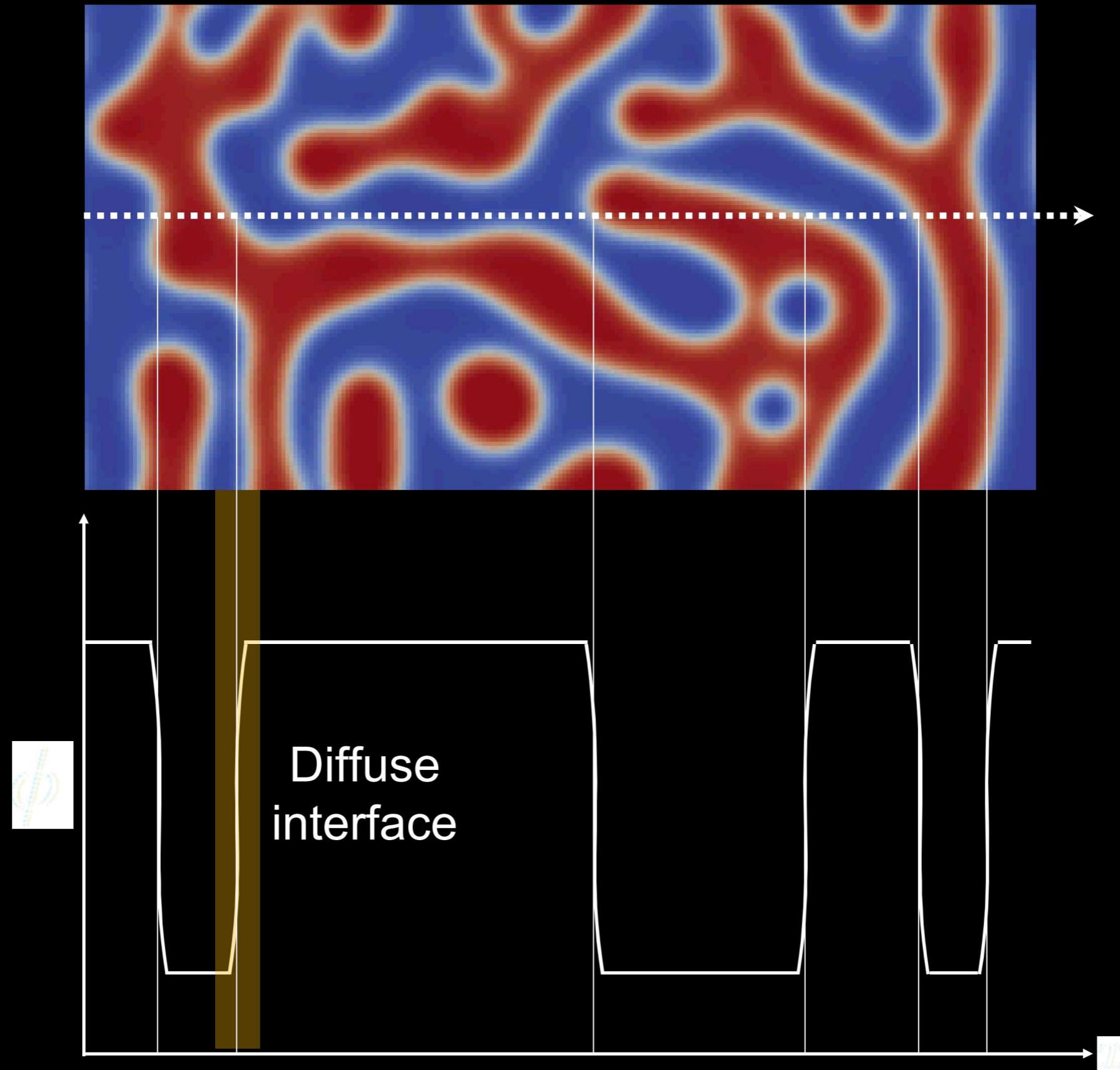
- Inter-diffusivity
- Atom dwell time
- Surface layer thickness
- Deposition rate

THE SYNTHESIS CHALLENGE

- **BROAD RANGE OF DEPOSITION CONDITIONS**
 - TARGET POWER
 - TEMPERATURE
 - SHADOWING
- **BROAD RANGE OF SPECIES**
 - SURFACE VS. BULK DIFFUSION
- **BEYOND SINGLE PHASE SYSTEMS**
 - COMPETITION IN PHASE ORDERING
 - ELASTIC MISMATCH



PHASE FIELD 101: MODELING MICROSTRUCTURE EVOLUTION



PHASE FIELD 101: MODELING MICROSTRUCTURE EVOLUTION

$$H^t := \int \left[f(\eta_1, \dots, \eta_p, c_1, \dots, c_p) + \sum_{i=1}^n \alpha_i (\nabla c_i)^2 + \sum_{i,j=1}^n \beta_{ij} \nabla_i \eta_k \nabla_j \eta_k \right] d\Omega$$

Allen-Cahn:
Non-conserved

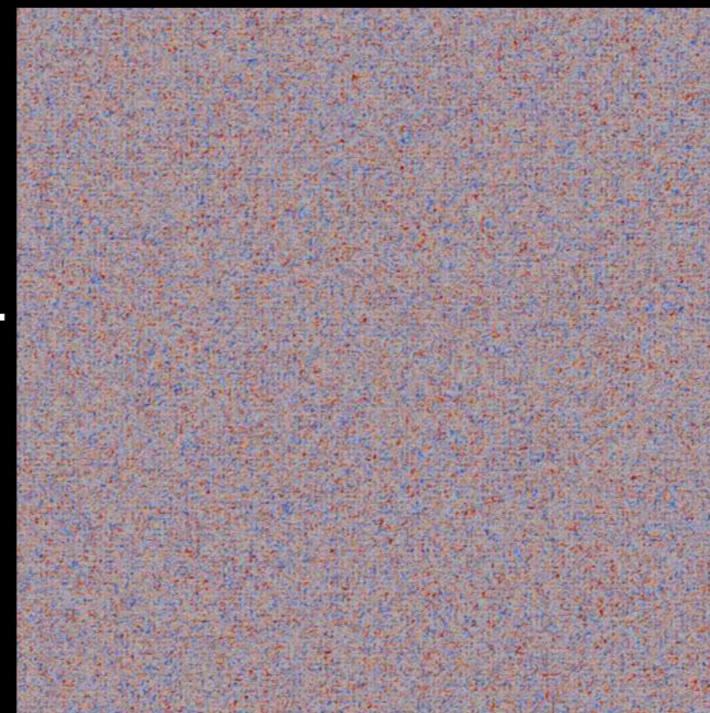
$$\frac{\partial \eta_p}{\partial t} = -M_{pq} \frac{\delta H^t}{\delta \eta_q}$$

Cahn-Hilliard:
Conserved

$$\frac{\partial c_i}{\partial t} = \nabla \cdot \left(M_{ij} \nabla \frac{\delta H^t}{\delta c_j} \right)$$

Grain growth

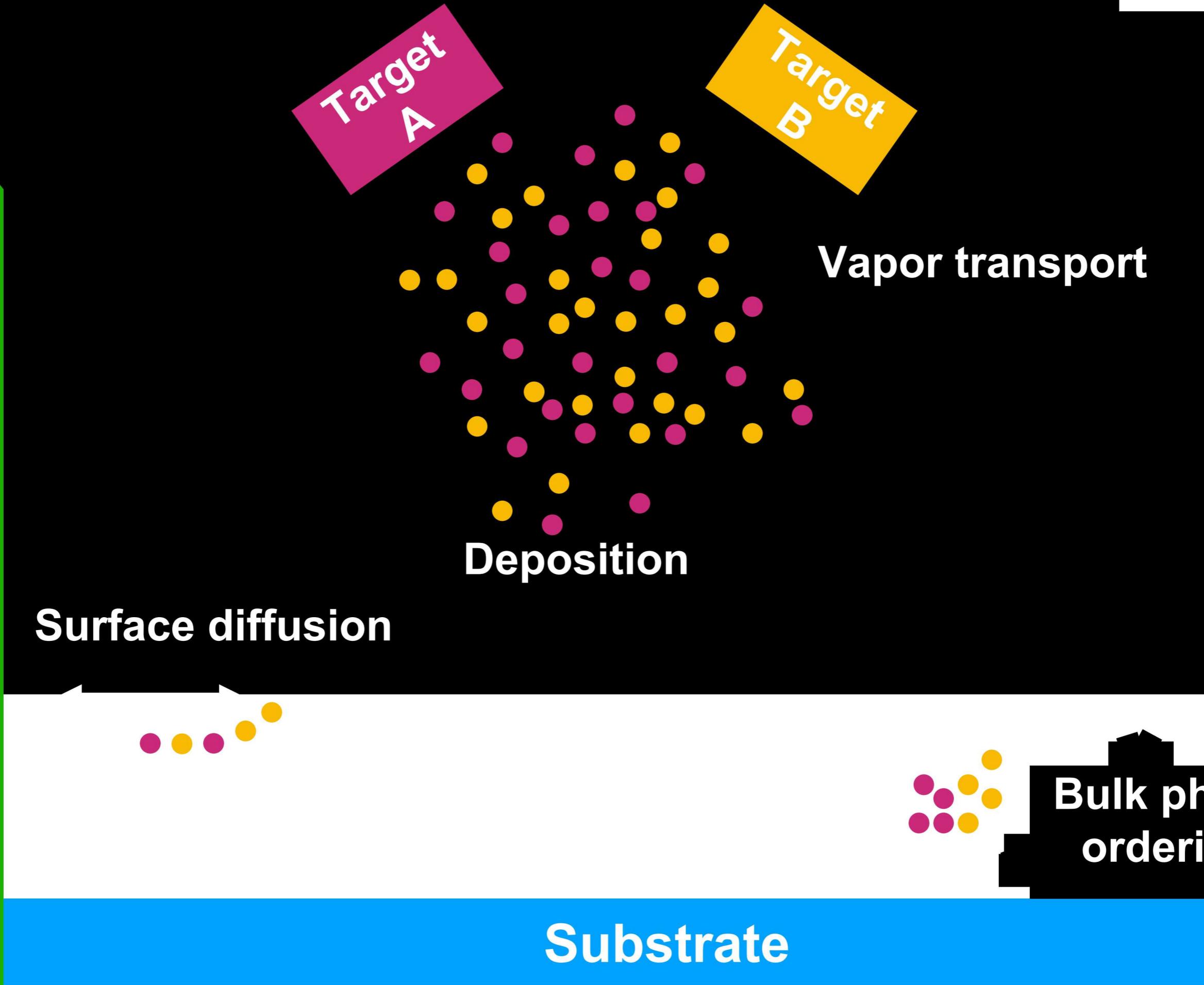
Spinodal
decomposition



Solidification

MODELING VAPOR DEPOSITION WITH PHASE FIELD

Growth direction



MODELING VAPOR DEPOSITION WITH PHASE FIELD

$$F = \int \left[f_\phi + \frac{\kappa_\phi^2}{2} (\nabla \phi)^2 + s(\phi) \left(f_c + \frac{\kappa_c^2}{2} (\nabla c)^2 \right) \right] d\Omega$$

Target A Target B

$$\frac{\partial \rho}{\partial t} = \nabla \cdot (D(\rho) \nabla \rho) + \nabla \cdot (\rho \vec{u}) + S(\vec{n})$$

Vapor transport

Vapor density (background pressure)

Deposition velocity (sputtering power)

Shadowing effect

$$\frac{\partial \phi}{\partial t} = \nabla \cdot \left(M(\phi) \nabla \frac{\delta F}{\delta \phi} \right) + S(\vec{n})$$

Deposition

$$\phi = -1$$

Surface diffusion

$$M_c(\phi, c) = M^{\text{bulk}} + M^{\text{surf}}$$



$$\phi = 1$$

$$\frac{\partial c}{\partial t} = \nabla \cdot \left(D(c) \nabla \frac{\delta F}{\delta t} \right)$$



Bulk phase ordering

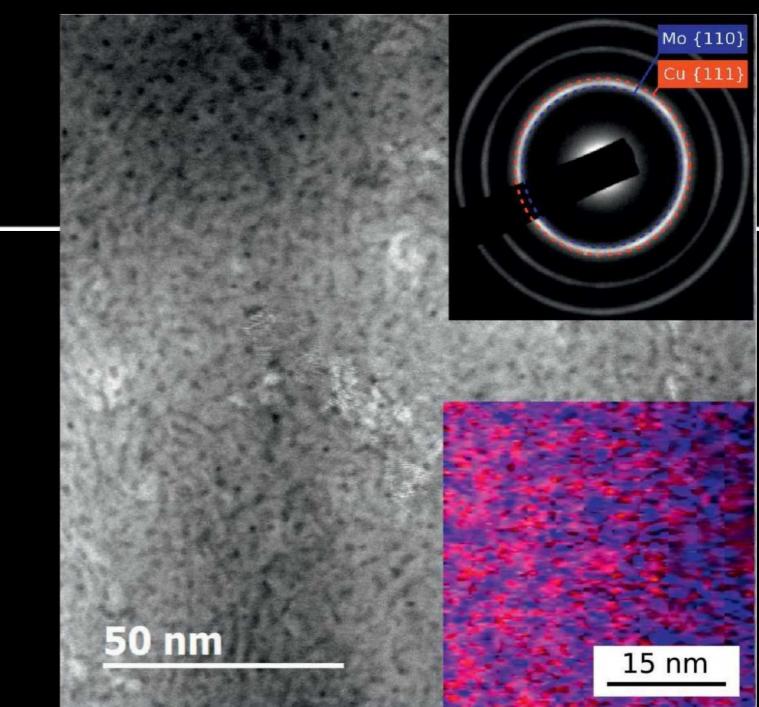
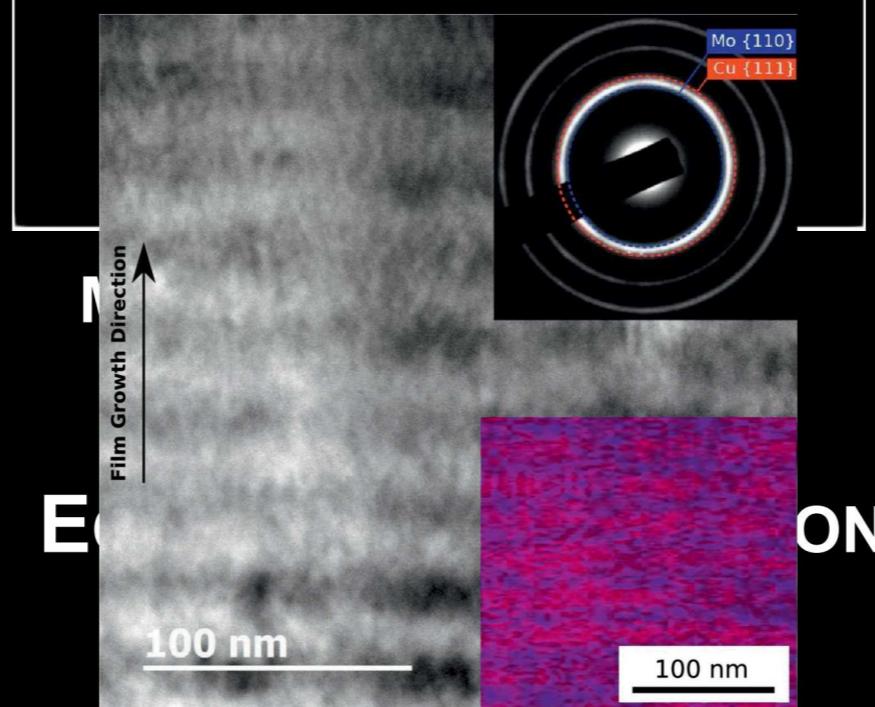
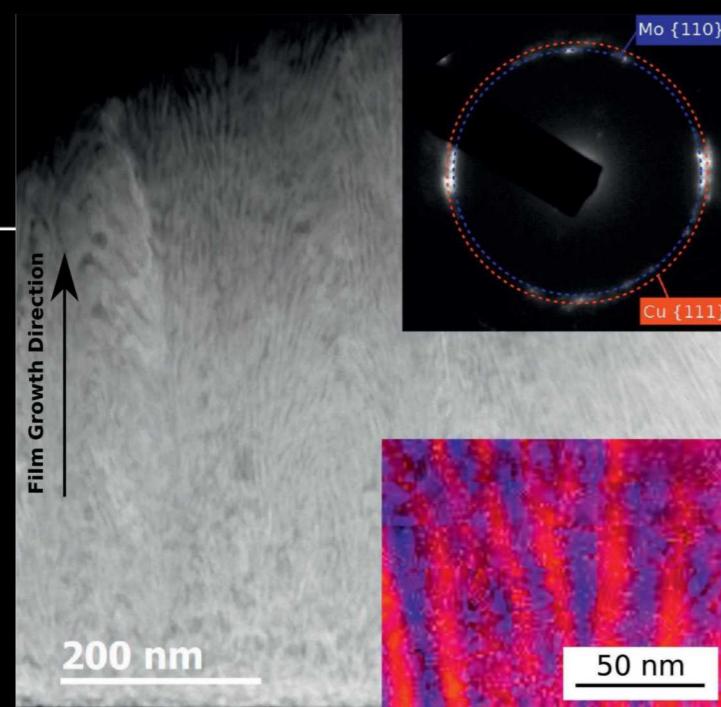
Substrate

SYNTHESIS ROUTES ENABLE ACCESS TO AT LEAST FOUR CLASSES OF CONCENTRATION MODULATIONS

Lateral
(LCM)

Vertical
(VCM)

Random
(RCM)



SYNTHESIS ROUTES ENABLE ACCESS TO AT LEAST FOUR CLASSES OF CONCENTRATION MODULATIONS

Raft-like lateral structure

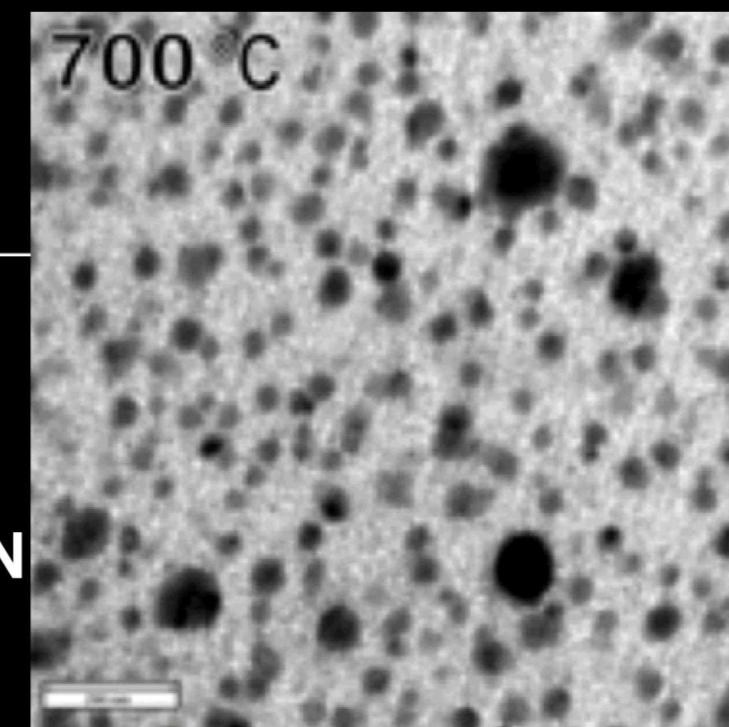
Nanoprecipitates
(NPCM)

Hybrid
(NPCM/LCM)

Slow deposition rate

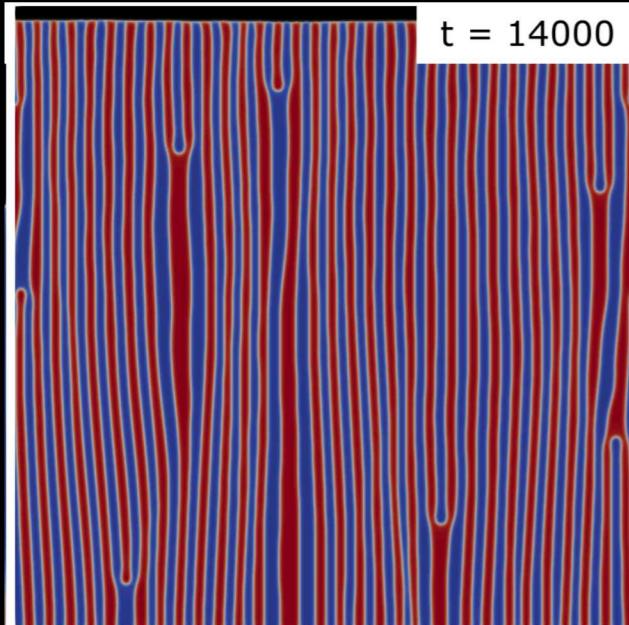
High deposition rate

UN
TION

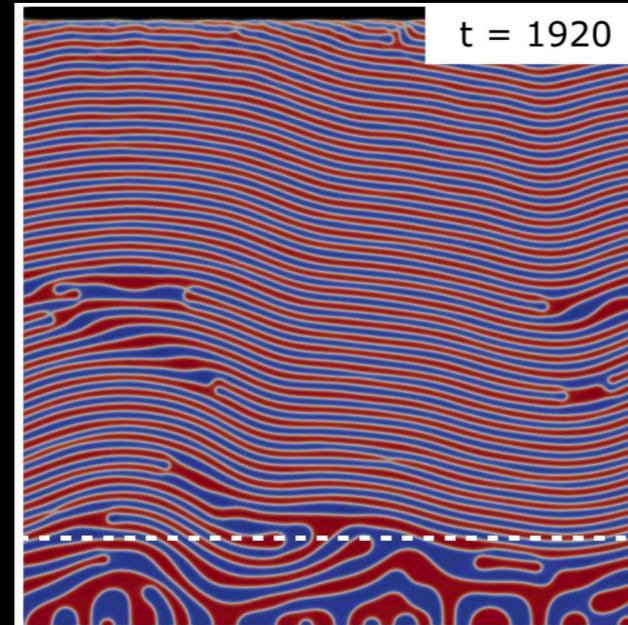


THE FORMATION AND EVOLUTION OF THESE MORPHOLOGIES STEM FROM COMPLEX COMPETITIONS

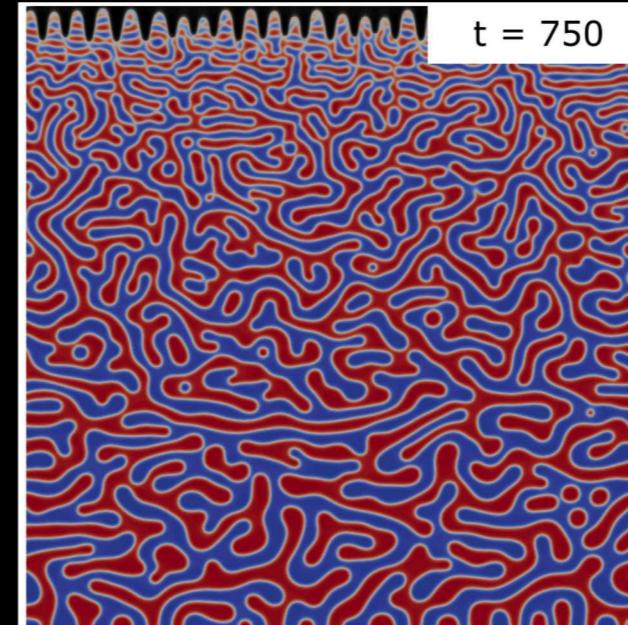
LCM



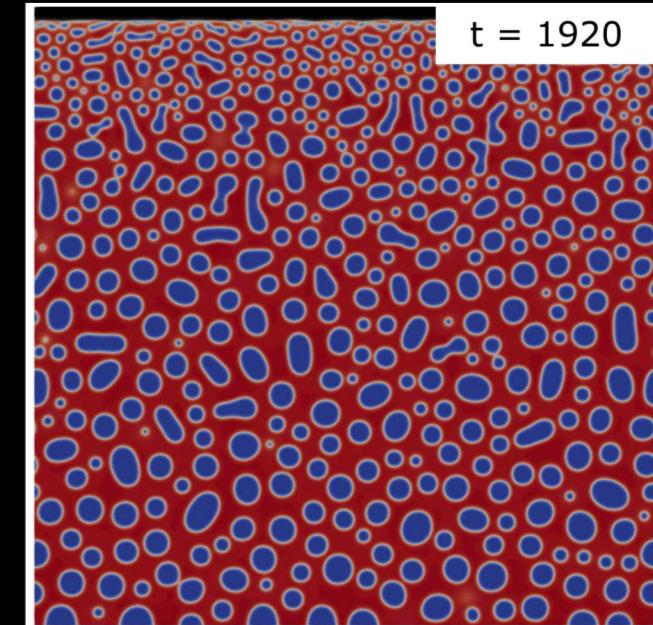
VCM



RCM



NPCM



- Surface and bulk ordering much faster than slow deposition
- Deposited material diffuses further and faster along surface before being buried by “next” layer of deposited material

- Critical thin thickness above which interfacial contribution is energetically favored
- “Frozen” bulk approximation

- Rapid transition to “bulk” regime
- Classical spinodal decomposition
- Formation of hillocks and surface roughness due to continuous perturbation of free surface

- Interparticle diffusion interactions (Ostwald ripening)
- Broader range of deposition conditions for unequal phase fraction

PHASE KINETICS HAS AN IMPACT ON THE RESULTING CONCENTRATION MODULATION

Majority species
with faster kinetics

Equivalent kinetics
between species

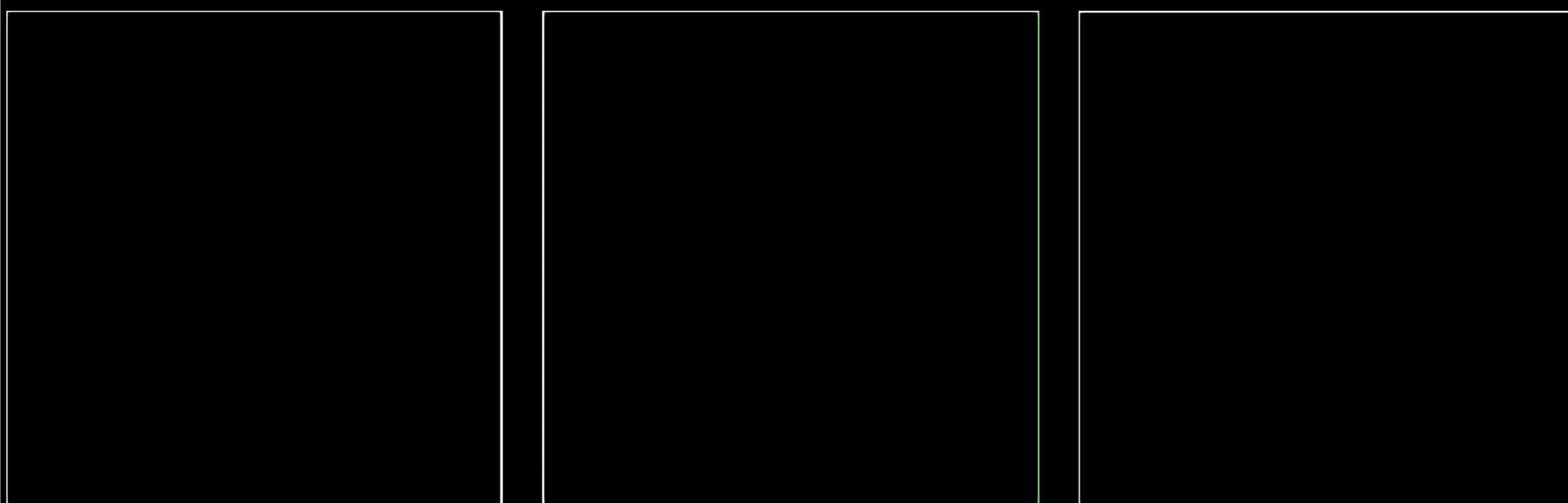
Minority species
with faster kinetics

ELASTIC EFFECTS CAN HAVE AN IMPACT ON THE SIZE AND SHAPE OF THE PHASE ORDERING

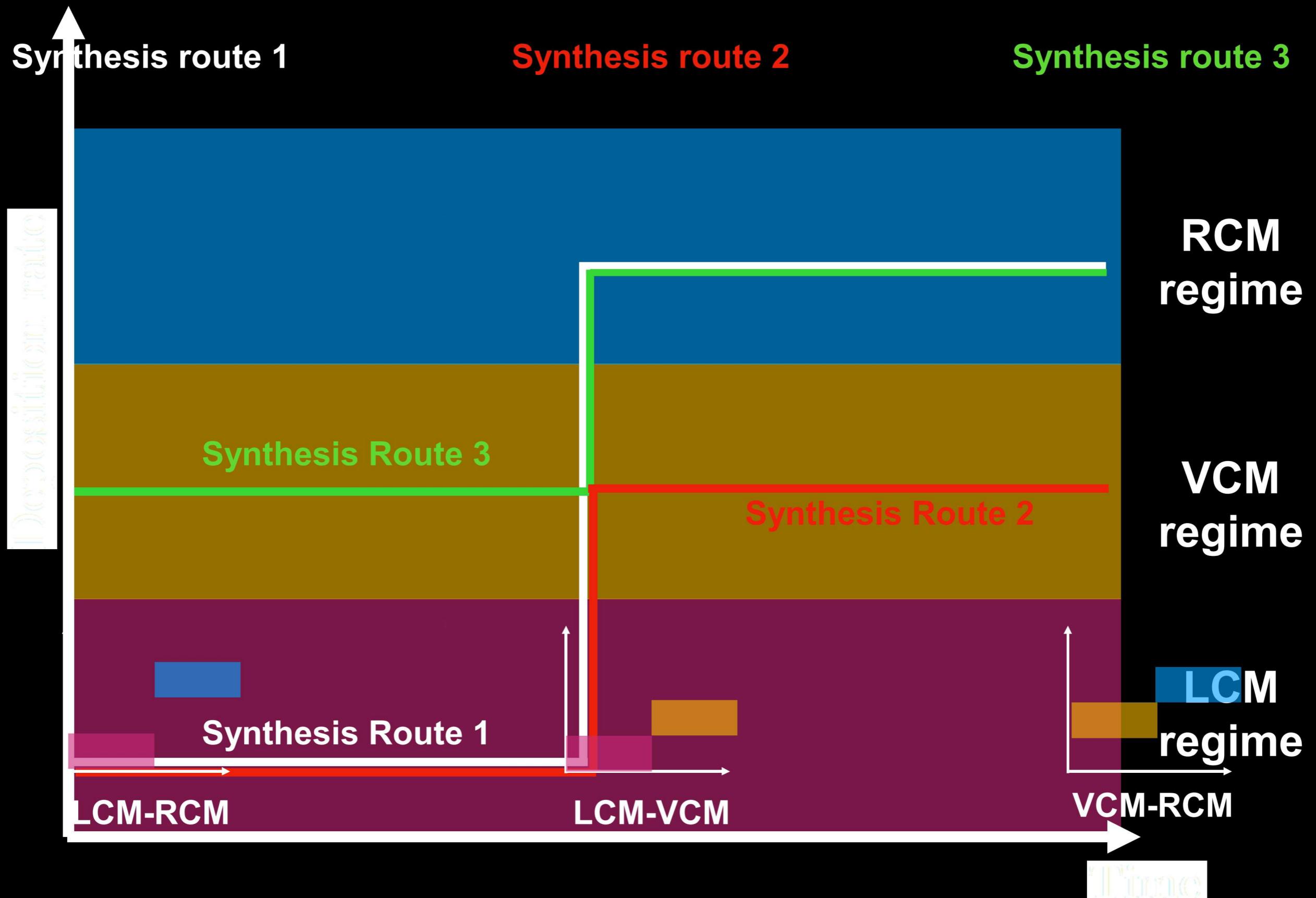
Majority species is soft

No elasticity

Majority species is hard

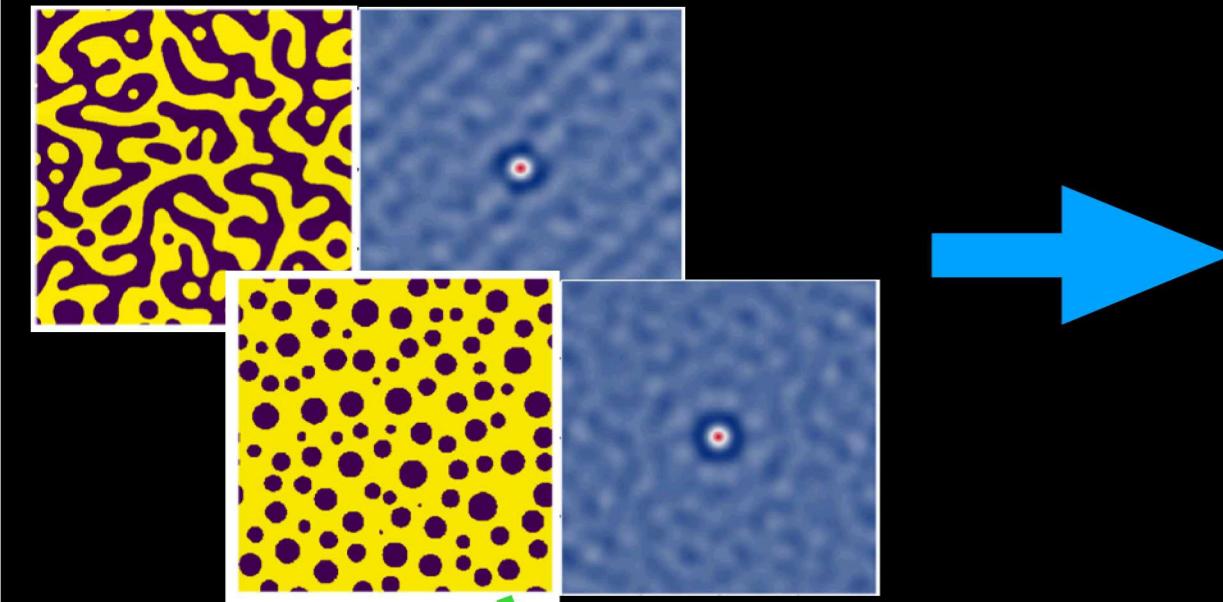


GOING BEYOND SIMPLE SYNTHESIS ROUTES... MULTI-MODULATION MORPHOLOGIES

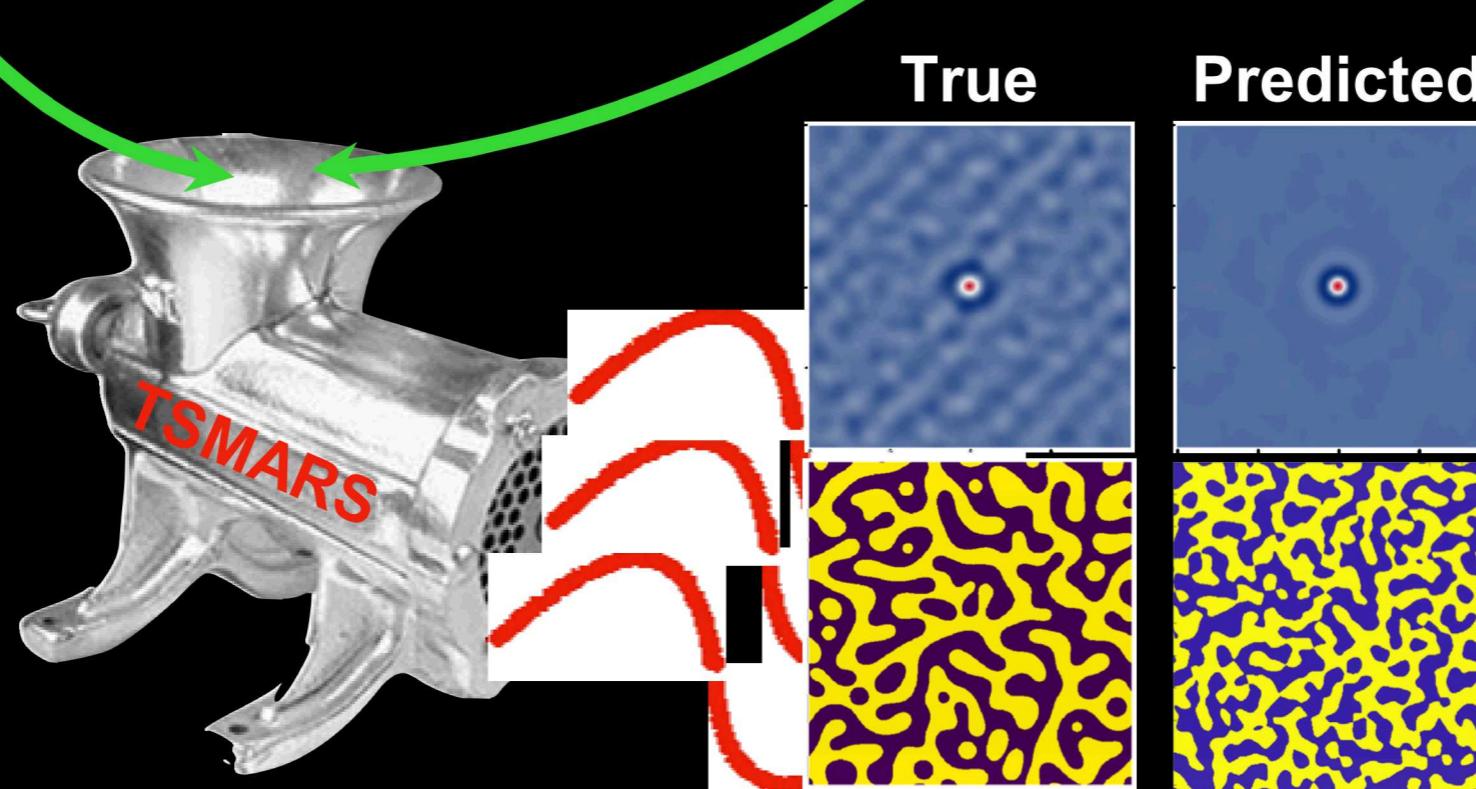
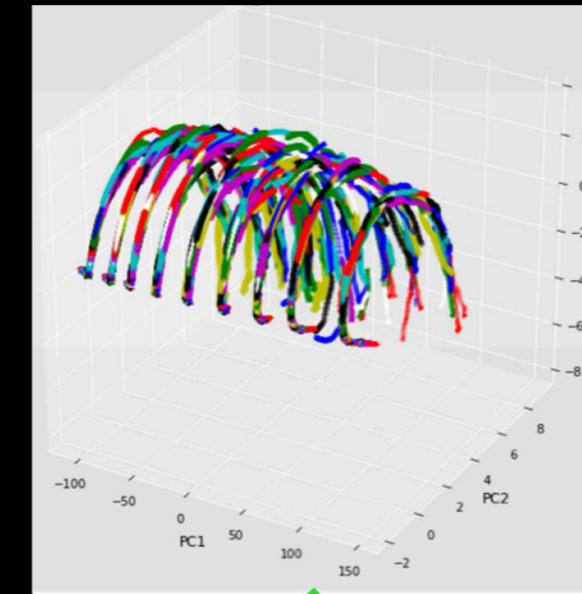


GOING BEYOND PHASE FIELD MODELING... MACHINE-LEARNED ENABLED PROCESS-STRUCTURE PREDICTIONS

Dimensionality reduction



Training data



- **Modeling of the growth of bicontinuous nanocomposites thin-films during PVD**
 - Generalized phase field model.
 - MEMPHIS: CINT user phase-field capability
 - Transport, surface diffusion, chemo-mechanical coupling during phase ordering
- **Insights into competing formation mechanisms**
 - Lateral, vertical, random, nanoprecipitate morphologies through specific combinations of deposition rate, phase fraction and phase properties
 - Guiding the choice of alloy species and deposition conditions to obtain specific nanostructured morphologies
 - Advanced regression/machine learning models to reverse engineering deposition conditions



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